

10/536706
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Amendment

AMENDMENT

To: Examiner of the Patent Office

1. Identification of the International Application
PCT/JP03/15200

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4. Item to be Amended: Claims

5. Subject Matter of Amendment

(1) Claim 7 should be cancelled.

6. List of Attached Documents

(1) Replacement sheet of page 17

10/536706

JCGC Rec'd PCT/PTO 27 MAY 2005

17

CLAIMS

1. A method of growing a p-type nitride semiconductor material by molecular beam epitaxy, the method comprising supplying bis(cyclopentadienyl)magnesium (Cp_2Mg) during the growth process.
2. A method as claimed in claim 1 wherein the nitride semiconductor material is p-type $(Ga,Al)N$.
3. A method as claimed in claim 1 or 2 and comprising supplying ammonia gas during the growth process.
4. A method as claimed in claim 1, 2 or 3 and comprising supplying ammonia gas, gallium and Cp_2Mg to a growth chamber, thereby to grow a layer of p-type GaN.
5. A method as claimed in claim 1, 2 or 3 and comprising supplying ammonia gas, aluminium, gallium and Cp_2Mg to a growth chamber, thereby to grow a layer of p-type AlGaN.
6. A method as claimed in any preceding claim, and comprising changing the supply rate of Cp_2Mg during the growth of the nitride semiconductor material.
7. (Cancelled)
8. A method as claimed in any preceding claim wherein the growth process is carried out at a temperature of at least 800°C.
9. A method as claimed in any preceding claim wherein the growth process is carried out at a temperature of at least 850°C.